

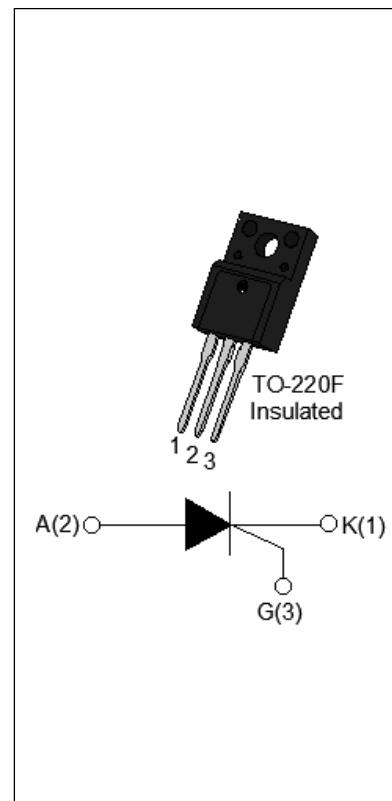


JCT1230F 30A SCR

Rev.A.1.0

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1230F SCR provide high dv/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1230F provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_T(\text{RMS})$	30	A
$V_{\text{DRM}} / V_{\text{RRM}}$	1200	V
I_{GT}	≤ 40	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	V
Average on-state current ($T_c \leq 46^\circ\text{C}$)	$I_{\text{T(AV)}}$	19	A
RMS on-state current ($T_c \leq 46^\circ\text{C}$)	$I_{\text{T(RMS)}}$	30	A
Non repetitive surge peak on-state current ($t_p=10\text{ms} , T_j=25^\circ\text{C}$)	I_{TSM}	370	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms} , T_j=25^\circ\text{C}$)		400	
I^2t value for fusing ($t_p=10\text{ms} , T_j=25^\circ\text{C}$)	I^2t	685	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{\text{GT}}, f=100\text{Hz}, T_j=125^\circ\text{C}$)	di/dt	200	$\text{A}/\mu\text{s}$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33\Omega$	-	-	40	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C R_L=3.3K\Omega$	0.25	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	120	mA
I_H	$I_T=1A$	-	-	100	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125^\circ C$	1500	-	-	V/ μs
t_{on}	$I_G=100mA I_A=1A I_R=100mA$ $T_j=25^\circ C$	-	5	-	μs
t_{off}		-	70	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit	
V_{TM}	$I_{TM}=60A$	$t_p=380\mu s$	$T_j=25^\circ C$	1.55	V
V_{TO}	Threshold voltage		$T_j=125^\circ C$	0.76	V
R_D	Dynamic resistance		$T_j=125^\circ C$	15	$m\Omega$
I_{DRM}	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ C$	8	μA
I_{RRM}			$T_j=125^\circ C$	3	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	2.1	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	60	$^\circ C/W$

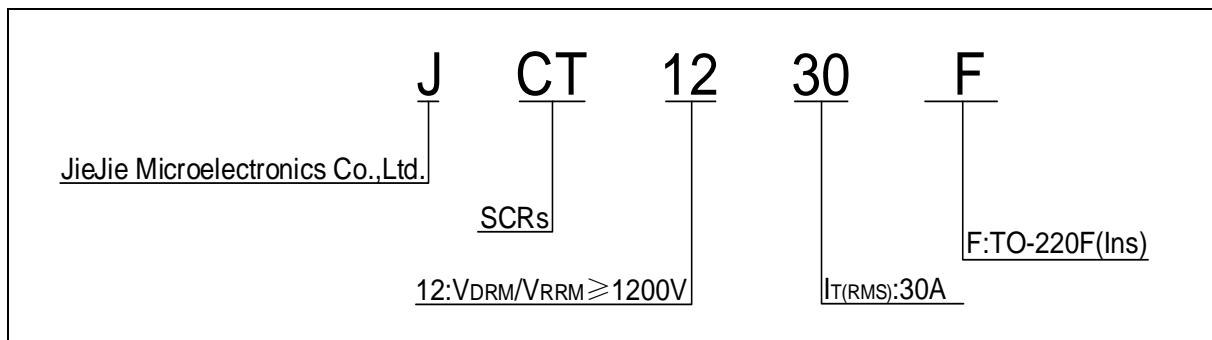
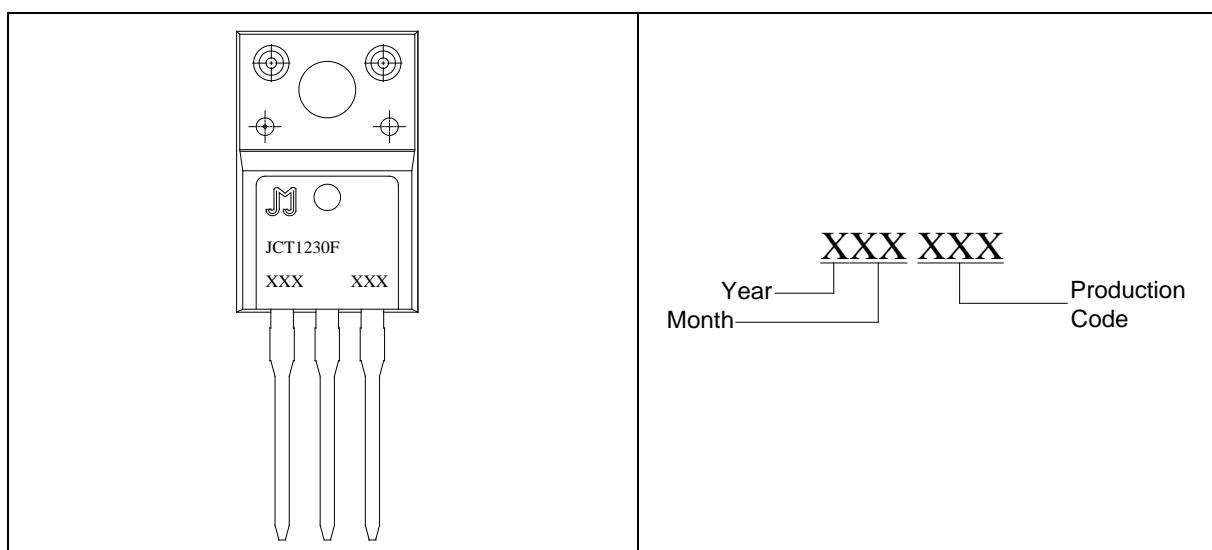
ORDERING INFORMATION**MARKING**

FIG.1 Maximum power dissipation versus RMS on-state current

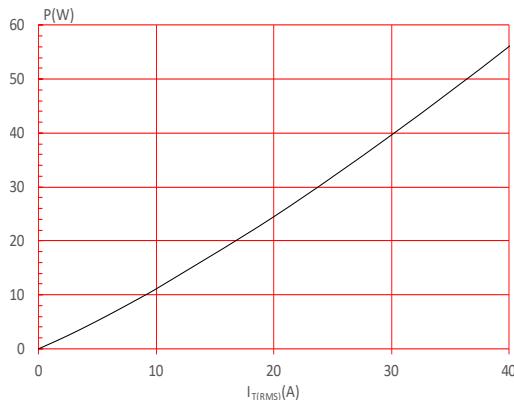


FIG.3: Surge peak on-state current versus number of cycles

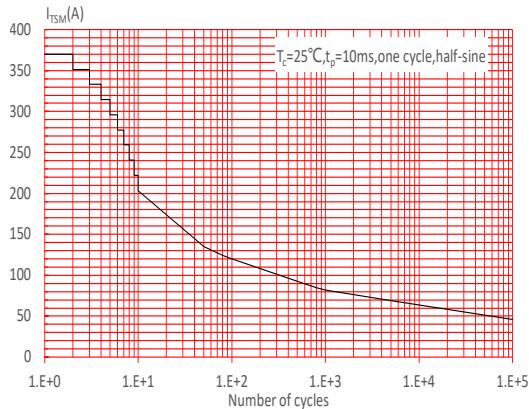


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($dl/dt < 200\text{A}/\mu\text{s}$)

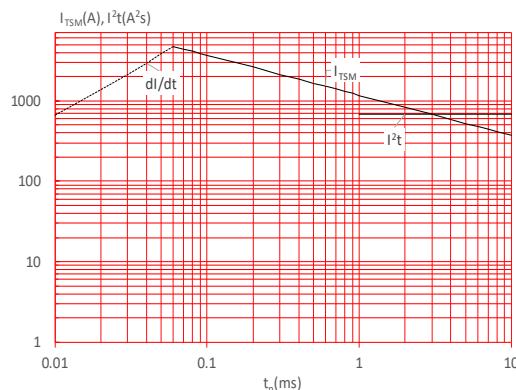


FIG.2: RMS on-state current versus case temperature

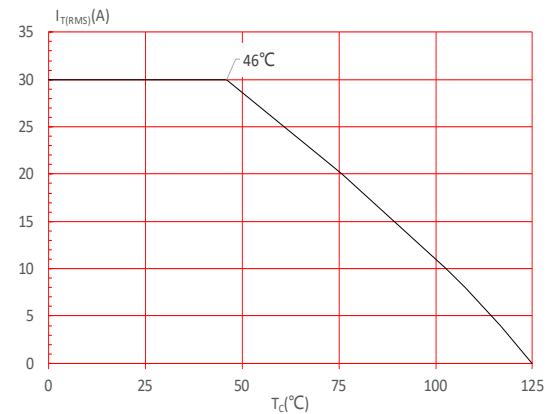


FIG.4: On-state characteristics

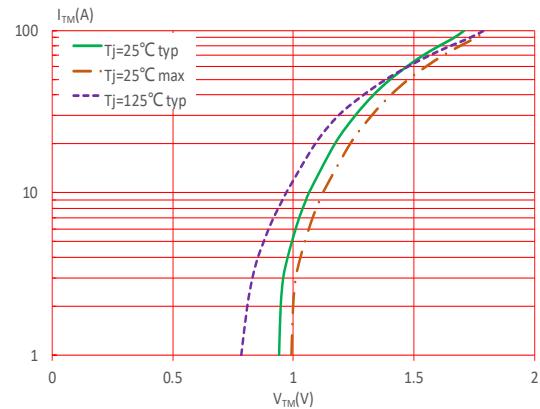


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

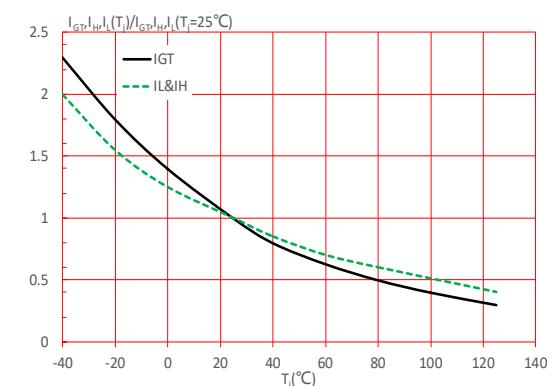
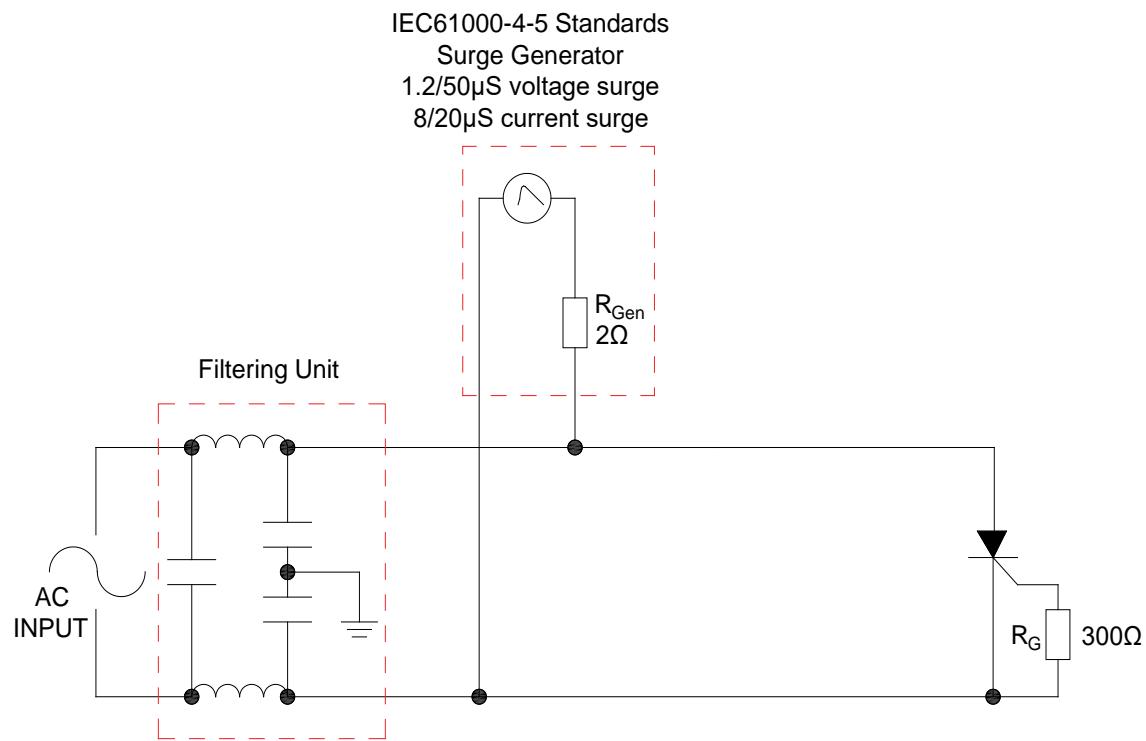


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

SHAPING AND SOLDERING PARAMETERS

Refer to «Instructions for installation of plastic-sealed in-line power devices» released by JieJie

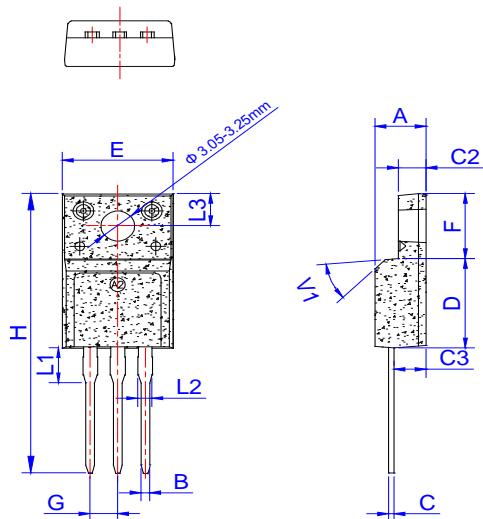
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1230F	1200	40	TO-220F(Ins)	50	Tube

Document Revision History

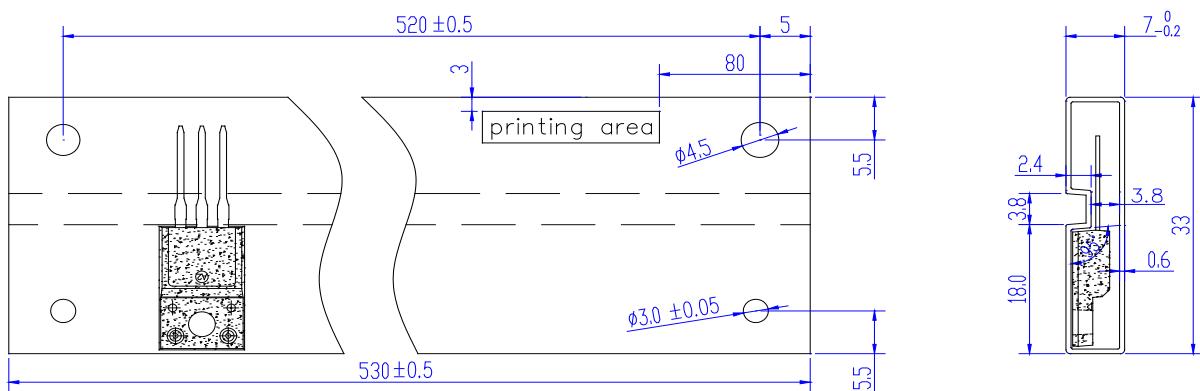
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.20		3.80	0.126		0.150
L2	1.14		1.70	0.045		0.067
L3	3.20		3.60	0.126		0.142
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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